2.25MHz 1A, Synchronous Step-Down Regulator

General Description

EML3025 is a high efficiency step down DC/DC converter. It features an extremely low quiescent current, which is suitable for reducing standby power consumption, especially for portable applications.

The device can accept input voltage from 2.5V to 5.5V and deliver up to 1A output current. High 2.25MHz switching frequency allows the use of small surface mount inductors and capacitors to reduce overall PCB board space. Furthermore, the built-in synchronous switch improves efficiency and eliminates external Schottky diode. EML3025 uses different modulation algorithms for various loading conditions: (1) Pulse Width Modulation (PWM) for low output voltage ripple and fixed frequency noise, (2) Pulse Frequency Modulation (PFM) for improving light load efficiency, and (3) Low Dropout (LDO) Mode for providing 100% duty cycle operation during heavy loading. Adopting low reference voltage design reduces regulated output to 0.6V. The adjustable version of this device is available in SOT-23-5 package.

Features

■ Achieve 97% efficiency

■ Input voltage: 2.5V to 5.5V

Output current up to 1A

■ Reference voltage: 0.6V

 \blacksquare Quiescent current 17 μ A with no load

■ Internal switching frequency: 2.25MHz

■ No Schottky diode needed

■ Low dropout operation: 100% duty cycle

■ Shutdown current < 1μ A

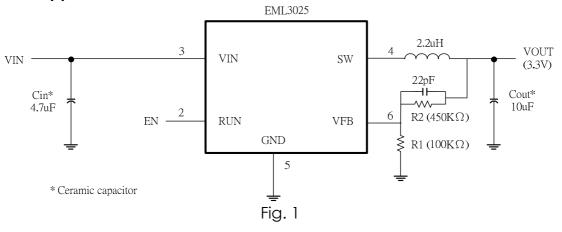
Excellent line and load transient response

Over-temperature protection

Applications

- Blue-Tooth devices
- Cellular and Smart Phones
- Personal Multi-media Player (PMP)
- Wireless networking
- Digital Still Cameras
- Portable applications

Typical Application

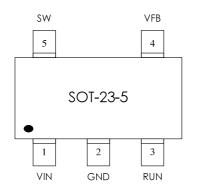


Elite Semiconductor Microelectronics Technology Inc.

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Package Configuration



EML3025-00VF05NRR

00 Adjustable

VF05 SOT-23-5 Package

NRR RoHS & Halogen free package

Commercial Grade Temperature

Rating: -40 to 85°C

Package in Tape & Reel

Order, Mark & Packing information

Package	Vout(V)	Product ID	Marking	Packing
SOT-23-5	adjustable	EML3025-00VF05NRR	5 4 3025 Tracking Code PINI DOT 1 2 3	Tape & Reel 3K units

Pin Functions

Pin Name	SOT-23-5	Function
MINI		Power Input Pin. Must be closely decoupled to GND pin with a 4.7µF or
VIN	'	greater ceramic capacitor.
GND	2	Ground Pin.
DIIN	3	Enable Pin. Minimum 1.2V to enable the device. Maximum 0.4V to shut
RUN		down the device.
VFB		Feedback Pin. Receives the feedback voltage from an external resistive
(Adjustable)		divider across the output.
VOUT	4	Output Voltage Pin. An internal resistive divider divides the output voltage
(Fixed voltage)		down for comparison to the internal reference voltage.
CIM	_	Switch Pin. Must be connected to Inductor. This pin connects to the drains
SW	5	of the internal main and synchronous power MOSFET switches.

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Absolute Maximum Ratings

Devices are subjected to fail if they stay above absolute maximum ratings.

Input Voltage 0.3V to 6V	Operating Temperature Range
RUN, VFB Voltages 0.3V to V _{IN}	Junction Temperature (Notes 1, 3) 150°C
SW Voltage $-0.3V$ to $(V_{IN} + 0.3V)$	Storage Temperature Range 65°C to 150°C
Lead Temperature (Soldering, 10 sec) 260°C	ESD Susceptibility HBM 2KV
	MM 200V

Thermal data

Package	Thermal resistance	Parameter	Value
SOT-23-5	heta JA (Note 4)	Junction-ambient	134.5°C/W
	θ JC (Note 5)	Junction-case	81°C/W

Electrical Characteristics

The lacktriangle denotes specifications which apply over the full operating temperature range, otherwise specifications are T_A = 25°C. V_{IN} = 3.6V unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Units
V _{IN}	Input Voltage Range			2.5		5.5	٧
I _{VFB}	Feedback Current					±100	nA
V_{FB}	Regulated Feedback Voltage			0.588	0.600	0.612	٧
Vout %	Output Voltage Accuracy	louт=100mA, Vin<3.0V		-3		+3	%
		I _{OUT} =100mA, Vin=3.0V to 5.5V	•	-3		+3	%
ΔV_{FB}	Reference Voltage Line Regulation	Vin=2.5V to 5.5V				0.4	%/V
ΔV_{OUT}	Output Voltage Line Regulation	Vin=2.5V to 5.5V				0.4	%/V
I _{PK}	Peak Inductor Current	$V_{FB} = 0.5V \text{ or } V_{OUT} = 90\%,$		1.5	2.3		Α
Is	PWM Quiescent Current (Note 2)	$V_{FB} = 0.5V \text{ or } V_{OUT} = 90\%$			205		μΑ
	PFM Quiescent Current	$V_{FB} = 0.65V \text{ or } V_{OUT} = 108\%$			17		μΑ
	Shutdown	$V_{RUN} = 0V, V_{IN} = 4.2V$			0.1	1	μΑ
fosc	Oscillator Frequency	V _{FB} = 0.6V or V _{OUT} = 100%		1.8	2.25	2.7	MHz
	Short-Circuit Oscillator Frequency	V _{FB} = 0V or V _{OUT} = 0V			1.5		MHz
R _{PFET}	R DS(ON) OF PMOS	I _{sw} = 100mA			0.24		Ω
R _{NFET}	R DS(ON) OF NMOS	$I_{SW} = -100 \text{mA}$			0.21		Ω
V _{UVLO}	Under Voltage Lock Out				1.8		٧
I _{LSW}	SW Leakage	$V_{RUN} = 0V$, $V_{SW} = 0V$ or 5V, $V_{IN} = 5V$				±1	μΑ
	Enable Threshold			1.2			V
V _{RUN}	Shutdown Threshold					0.4	V
I _{RUN}	RUN Leakage Current		•			±1	μ A

Note 1: T_J is a function of the ambient temperature T_A and power dissipation P_D ($T_J = T_A + (P_D) * (165°C/W)$).

Note 2: Dynamic quiescent current is higher due to the gate charge being delivered at the switching frequency.

Note 3: This IC has a built-in over-temperature protection to avoid damage from overloaded conditions.

Note 4: θ JA is measured in the natural convection at TA=25°C on a highly effective thermal conductivity test board (2 layers , 2SOP) according to the JEDEC 51-7 thermal measurement standard.

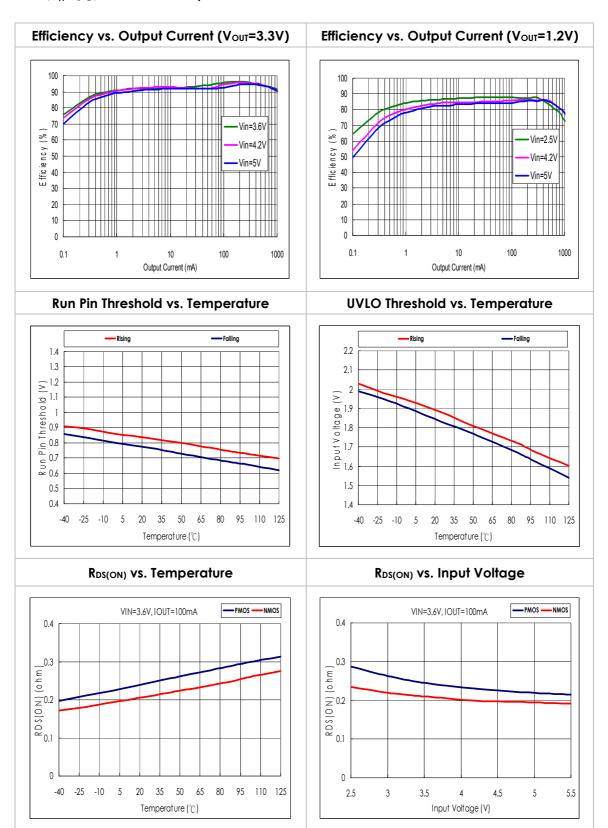
Note 5: $\, \theta \, {
m JC} \, {
m represents}$ the heat resistance between the chip and the package top case.

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Typical Performance Characteristics

 V_{IN} =3.6V, T_A =25°C, unless otherwise specified

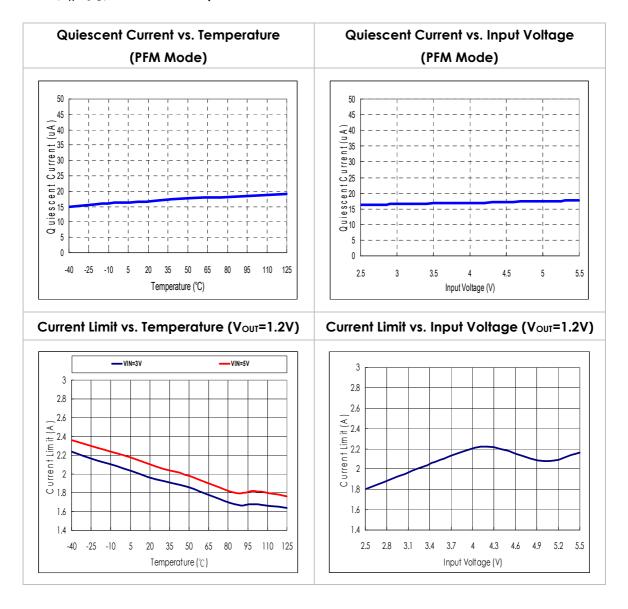


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Typical Performance Characteristics (cont.)

 V_{IN} =3.6V, T_{A} =25°C, unless otherwise specified

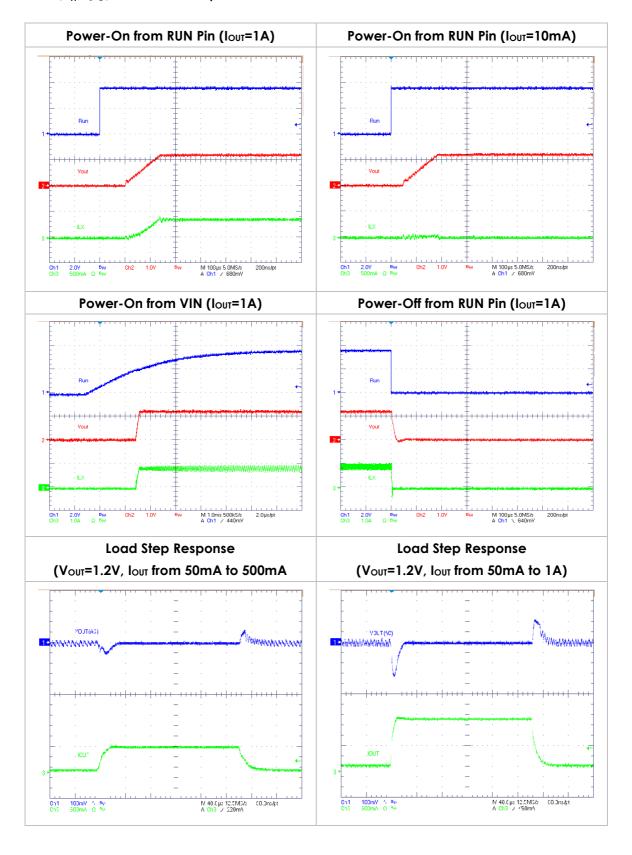


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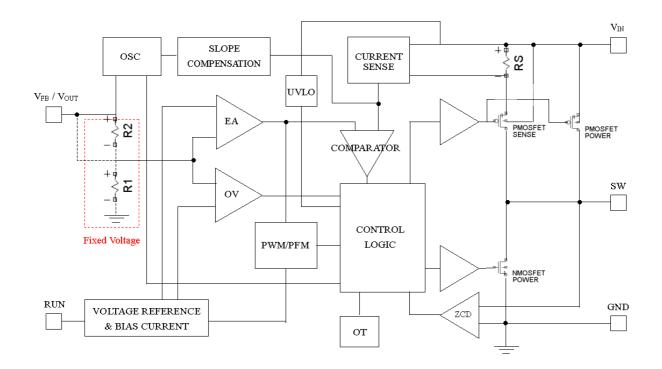
Typical Performance Characteristics (cont.)

 V_{IN} =3.6V, T_{A} =25°C, unless otherwise specified





Functional Block Diagram



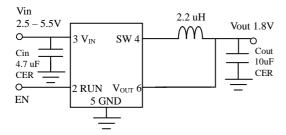
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Applications

The typical application circuit of adjustable version is shown in Fig.1.

Fixed voltage version is shown below:



Inductor Selection

Inductor ripple current and core saturation current are the two main factors that decide the Inductor value. A low DCR inductor is preferred.

CIN and COUT Selection

A low ESR input capacitor can prevent large voltage transients at V_{IN} . The RMS current of input capacitor is required larger than I_{RMS} calculated by:

$$I_{RMS} \stackrel{\cong}{=} I_{OMAX} \frac{\sqrt{V_{OUT}(V_{IN} - V_{OUT})}}{V_{IN}}$$
 Eq. 1

ESR is an important parameter to select C_{OUT} , which can be seen in the following output ripple V_{OUT} equation:

$$\Delta V_{OUT} \cong \Delta I_{L} \left(ESR + \frac{1}{8 \cdot f \cdot C_{OUT}} \right)$$
 Eq. 2

Cheaper and smaller ceramic capacitors with higher capacitance values are now commercially available. These ceramic capacitors have low ripple currents, high voltage ratings and low ESR which make them suitable for switching regulator applications. It is feasible to optimize very low output ripples by Cout since Cout does not affect the internal control loop stability. X5R or X7R types are recommended since they have the best temperature and voltage characteristics of all ceramics capacitors.

Output Voltage (EML3025 adjustable)

In the adjustable version, the output voltage can be determined by:

$$V_{OUT} = 0.6 V \left(1 + \frac{R_2}{R_1} \right)$$
 Eq. 3

Thermal Considerations

Although the thermal shutdown circuit is designed in EML3025 to protect the device from thermal damage, the total power dissipation that EML3025 can sustain depends on the thermal capability of the package. The formula to ensure the safe operation is shown in note 1 on page 5.

To avoid the EML3025 from exceeding the maximum junction temperature, the user should perform some thermal analysis during PCB design.

Guidelines for PCB Layout

To ensure proper operation of the EML3025, please note the following PCB layout guidelines:

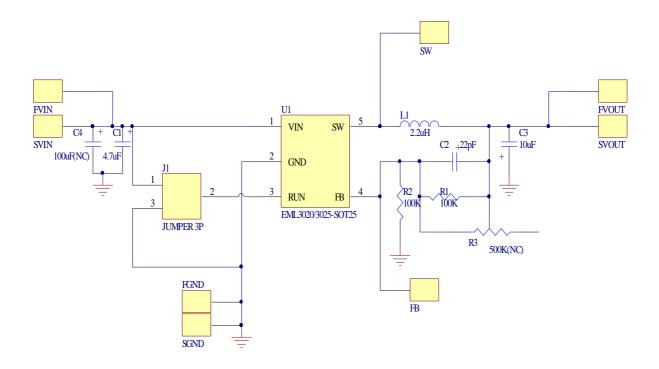
- 1. The GND, SW and the VIN trace should be kept short, direct and wide.
- 2. VFB pin must be connected directly to the feedback resistors. Resistive divider R1/R1 must be connected parallel to the output capacitor C_{OUT} .
- 3. The Input capacitor C_{IN} must be connected to the pin VIN as close as possible.
- 4. Keep SW node away from the sensitive VFB node since this node has high frequency and voltage swing.
- 5. Keep the (-) plates of C_{IN} and C_{OUT} as close as possible.

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Applications

Typical schematic for PCB layout



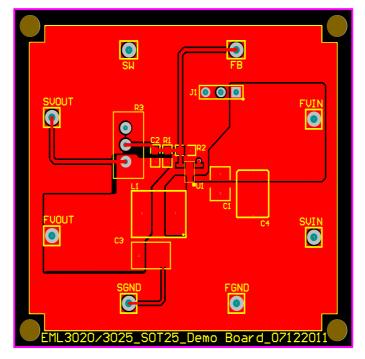
Note.

R3 and C4 are reserved locations for testing purposes. They are removed during normal applications.

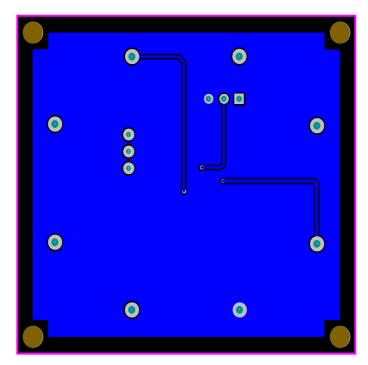
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Typical schematic for PCB layout (cont.)



Top Layer

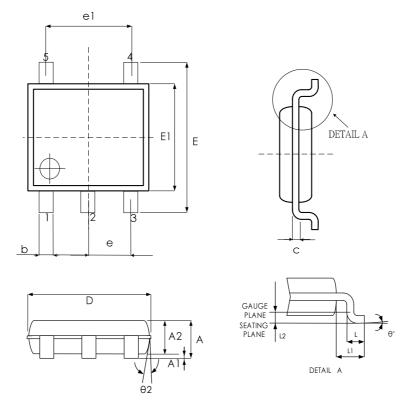


Bottom Layer



Package Information

SOT-23-5



SYMBPLS	MIN.	NOM.	MAX.
Α	1.05	1.20	1.35
A1	0.05	0.10	0.15
A2	1.00	1.10	1.20
В	0.30	_	0.50
С	0.08	_	0.20
D	2.80	2.90	3.00
E	2.60	2.80	3.00
E1	1.50 1.60		1.70
E	0.95 BSC		
el	1.90 BSC		
L	0.30 0.45		0.55
L1	0.60 REF		
θ°	0	5	10
θ2°	6	8	10

UNIT: MM



Revision History

Revision	Date	Description
0.1	2011.10.12	Original.
1.0	2015.03.11	Revise version to 1.0 & remove preliminary word

EML3025



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